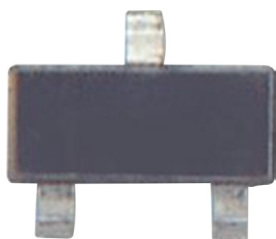


Switching Diode

SOT-23

RoHS
Compliant



Features:

- Silicon Planar Epitaxial High-Speed Diode

Absolute Maximum Ratings:

Parameters	Symbol		Value	Units
Continuous Reverse Voltage	V_R	Maximum	75	V
Repetitive Peak Reverse Voltage	V_{RRM}		85	
Repetitive Peak Forward Current	I_{FRM}		500	mA
Junction Temperature	T_j		150	°C
Forward Voltage at $I_F = 50\text{mA}$	V_F	<	1	V
Reverse Recovery Time When Switched from $I_F = 10\text{mA}$ to $I_R = 10\text{mA}$; $R_L = 100\Omega$; measured at $I_R = 1\text{mA}$	t_{rr}	<	4	nS
Recovery Charge When Switched from $I_F = 10\text{mA}$ to $V_R = 5\text{V}$; $R_L = 100\Omega$	Q_S	<	45	pC

Ratings (per diode) (at $T_A = 25^\circ\text{C}$ unless otherwise specified)

Limiting Values	Symbol		Value	Units
Continuous Reverse Voltage	V_R	Maximum	75	V
Repetitive Peak Reverse Voltage	V_{RRM}		85	
Forward Current (DC)	I_F		215	mA
Repetitive Peak Forward Current	I_{FRM}		500	

Switching Diode

SOT-23



Limiting Values	Symbol		Value	Units
Non-Repetitive Peak Forward Current (per Crystal) t = 1μs t = 1ms t = 1s	I_{FSM}	Maximum	4 1 0.5	A
Storage Temperature Range	T_{stg}	-	-55 to +150	°C
Junction Temperature	T_j	Maximum	150	

Thermal Resistance

From Junction To Ambient	$R_{th(j-a)}$	=	500	K/W
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Characteristics (per diode) (at $T_A = 25^\circ\text{C}$ unless otherwise specified)

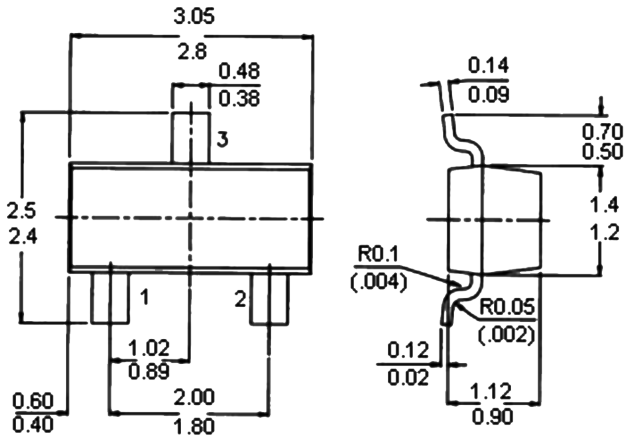
Limiting values	Symbol		Value	Units
$T_j = 25^\circ\text{C}$ unless otherwise specified	-	-	-	-
Forward voltage $I_F = 1\text{mA}$ $I_F = 10\text{mA}$ $I_F = 50\text{mA}$ $I_F = 150\text{mA}$	V_F	<	715 855 1,000 1,250	mV
Reverse current $V_R = 25\text{V}; T_j = 150^\circ\text{C}$ $V_R = 75\text{V}$ $V_R = 75\text{V}; T_j = 150^\circ\text{C}$	I_R	<	30 1 50	mA
Diode capacitance $V_R = 0; f = 1\text{MHz}$	C_d	<	2	pF
Forward recovery voltage when switched to $I_F = 10\text{mA}; t_f = 20\text{ns}$	V_{fr}	<	1.75	V
Reverse recovery time When switched from $I_F = 10\text{mA}$ to $I_R = 10\text{mA}$; $R_L = 100\Omega$; measured at $I_R = 1\text{mA}$	trr		4	nS
Recovery charge When switched from $I_F = 10\text{mA}$ to $V_R = 5\text{V}$; $R_L = 100\Omega$	QS		45	pC

Switching Diode

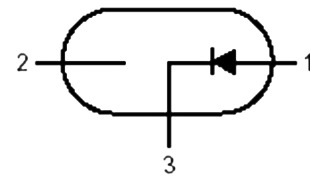
SOT-23



Package Outline Details



Dimensions : Millimetres



Pin Configuration

1. Anode
2. NC
3. Cathode

Part Number Table

Description	Part Number
Diode, Switching, SOT-23	TBAS16

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